NEC

PNP SILICON DARLINGTON TRANSISTOR

2SB1149

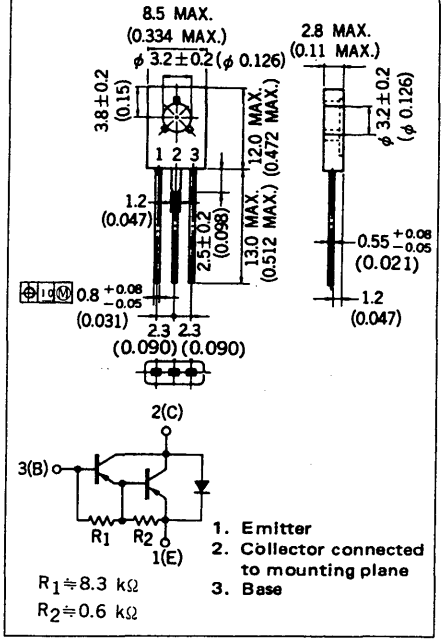
DESCRIPTION The 2SB1149 is a darlington transistor built-in dumper diode at E-C.

It is suitable for use to operate from IC without predriver, such as hammer driver.

FEATURES

- High DC Current Gain.
- Low Collector Saturation Voltage.
- Built-in a dumper diode at E-C.
- High Power Dissipation: P_T = 1.3 W (at T_a = 25 °C)

PACKAGE DIMENSIONS
in millimeters (inches)



ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

- Storage Temperature . . . . . −55 to +150 °C
- Junction Temperature . . . . . 150 °C Maximum

Maximum Power Dissipations

- Total Power Dissipation (T_a = 25 °C) . . . . . 1.3 W
- Total Power Dissipation (T_c = 25 °C) . . . . . 15 W

Maximum Voltages and Currents (T_a = 25 °C)

- V_{CBO} Collector to Base Voltage . . . . . −100 V
- V_{CEO} Collector to Emitter Voltage . . . . . −100 V
- V_{EBO} Emitter to Base Voltage . . . . . −8.0 V
- $I_{C(DC)}$ Collector Current . . . . . ∓3.0 A
- $I_{C(pulse)}$* Collector Current . . . . . ∓5.0 A

* PW ≦ 10 ms, Duty Cycle ≦ 50 %

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
h_{FE1}**	DC Current Gain	2000		15000	–	V_{CE} = −2.0 V, I_C = −1.5 A
h_{FE2}**	DC Current Gain	1000			–	V_{CE} = −2.0 V, I_C = −3.0 A
t_{on}	Turn On Time		0.5		μs	I_C = −1.5 A, R_L = 27 Ω
t_{stg}	Storage Time		2.0		μs	I_{B1} = −I_{B2} = −1.5 mA, V_{CC} ≒ −40 V
t_f	Fall Time		1.0		μs	See Test Circuit.
I_{CBO}	Collector Cutoff Current			−10	μA	V_{CB} = −100 V, I_E = 0
I_{EBO}	Emitter Cutoff Current			−1.0	mA	V_{EB} = −5.0 V, I_C = 0
$V_{CE(sat)}$**	Collector Saturation Voltage		−0.9	−1.2	V	I_C = −1.5 A, I_B = −1.5 mA
$V_{BE(sat)}$**	Base Saturation Voltage		−1.5	−2.0	V	I_C = −1.5 A, I_B = −1.5 mA

** Pulsed / PW ≦ 350 μs, Duty Cycle ≦ 2 %

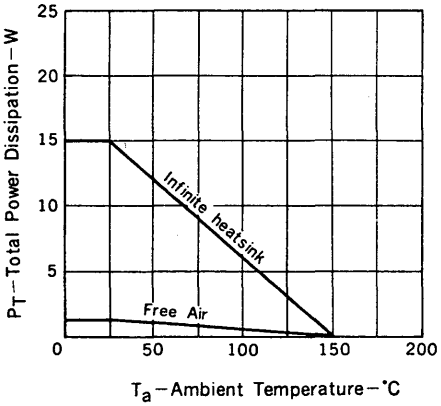
Classification of h_{FE1}

Rank	M	L	K
Range	2000 to 5000	3000 to 7000	5000 to 15000

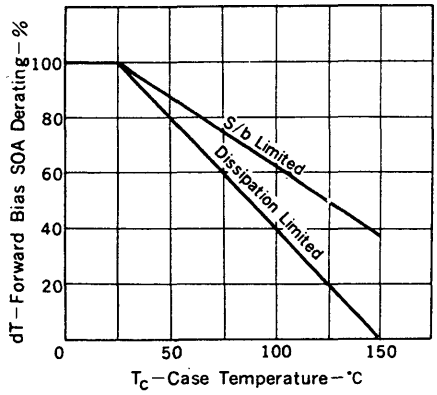
Test Conditions: V_{CE} = −2.0 V, I_C = −1.5 A

TYPICAL CHARACTERISTICS (T_a = 25 °C)

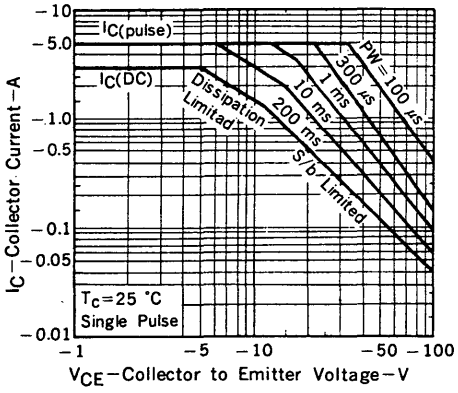
TOTAL POWER DISSIPATION vs. AMBINET TEMPERATURE



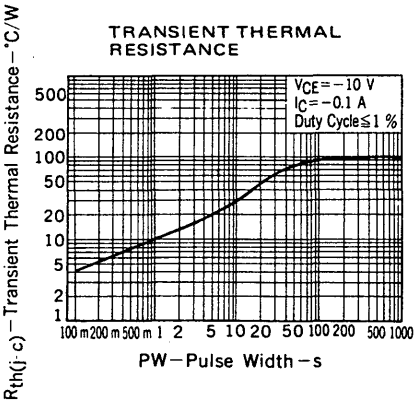
DERATING CURVE OF SAFE OPERATING AREA



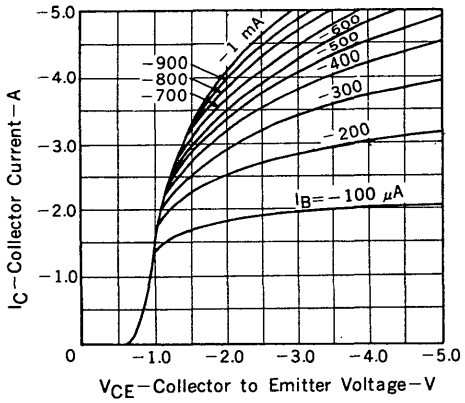
FORWARD BIAS SAFE OPERATING AREA



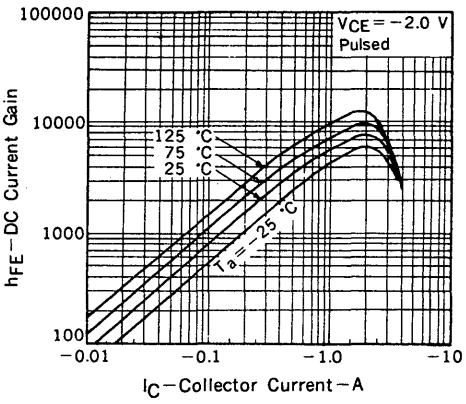
TRANSIENT THERMAL RESISTANCE



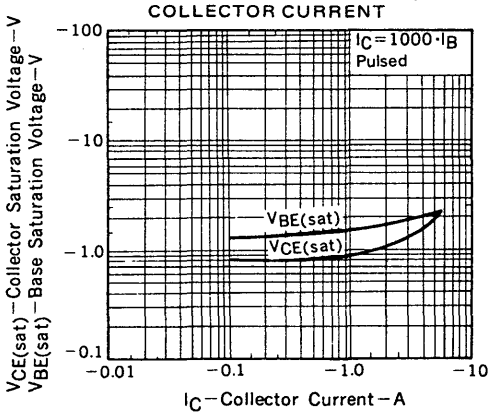
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



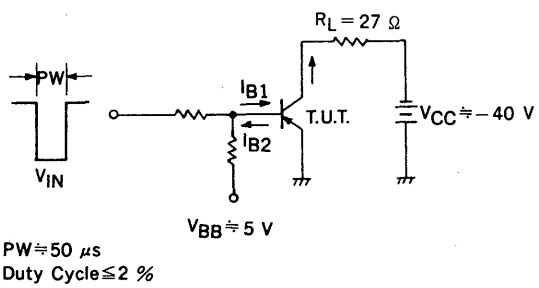
DC CURRENT GAIN vs. COLLECTOR CURRENT



BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



SWITCHING TIME (t_{on}, t_{stg}, t_f) TEST CIRCUIT



PW ≒ 50 μs
Duty Cycle ≦ 2 %